

In the Claims: Please amend claims 1, 10, 15, and 34, and add new claims 62-71 as follows:

a1  
Del B1

1. (Amended) A field emission display baseplate comprising:  
 a substrate;  
 a plurality of spaced-apart conductors formed on the substrate;  
 a plurality of spaced-apart emitter bodies comprising a high resistivity material formed on the conductors;  
 a porous silicon dioxide dielectric layer formed on the substrate and the conductors, the porous silicon dioxide layer having respective openings coaxial with the emitter bodies;  
 an extraction grid formed on the porous silicon dioxide layer and including respective openings coaxial with the emitter bodies;  
 [;]and  
 an emitter tip formed on each of the emitter bodies in the extraction grid opening, the tip formed from a material having a work function or electron affinity of less than four electron volts.

Del B2  
C2 Cont

10. (Amended) A field emission display baseplate comprising:  
 a substrate;  
 a plurality of conductors formed on the substrate;  
 a plurality of emitters each formed on one of the plurality of conductors;  
 a porous silicon dioxide dielectric layer formed by anodization on the substrate and the conductors;  
 an extraction grid formed on the dielectric layer and including an opening;  
 an opening formed in the dielectric layer coaxial with the opening in the extraction grid;  
 an emitter body comprising a high resistivity material formed in the opening in the porous silicon dioxide layer; and

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an emitter tip formed on the emitter body and in the extraction grid opening, the tip formed from a material having a work function or electron affinity of less than four electron volts.

13. (Amended) The baseplate of claim 10, wherein the porous silicon dioxide comprises porous silicon dioxide prepared by chemical etching of polycrystalline silicon followed by oxidation of the etched polycrystalline silicon.

34. (Amended) A computer system comprising:  
 a central processing unit;  
 a memory device coupled to the central processing unit, the memory device storing instructions and data for use by the central processing unit;  
 an input interface; and  
 a display, the display comprising:  
 a cathodoluminescent layer formed on a conductive surface of a transparent faceplate;  
 a substrate disposed parallel to and near the cathodoluminescent layer formed on the faceplate;  
 a plurality of conductors formed on the substrate;  
 a plurality of emitters formed on the conductors;  
 a porous silicon dioxide layer formed on the substrate and the [columns] conductors, the porous silicon dioxide layer including openings each formed about one of the emitters, the porous layer formed by oxidation of [porous] polycrystalline silicon; and  
 an extraction grid formed on the porous silicon dioxide layer and including openings each coaxial with one of the openings in the porous silicon dioxide layer.

Please add the following new claims

<sup>10</sup>  
--~~62~~. The baseplate of claim 1 wherein the emitter tip comprises SiC.

<sup>11</sup>  
~~63~~. The baseplate of claim 1 wherein the emitter tip comprises Zr.

<sup>12</sup>  
~~64~~. The baseplate of claim 1 wherein the emitter tip comprises La.

<sup>13</sup>  
~~65~~. The baseplate of claim 1 wherein the emitter tip comprises Zn.

<sup>14</sup>  
~~66~~. The baseplate of claim 1 wherein the emitter tip comprises TiN.

<sup>15</sup>  
~~67~~. The baseplate of claim 1 wherein the emitter tip comprises LaB<sub>6</sub>.

<sup>16</sup>  
~~68~~. The baseplate of claim 1 wherein the emitter tip comprises diamond.

<sup>17</sup>  
~~69~~. The baseplate of claim 1 wherein the emitter tip comprises silicon oxycarbide.

<sup>34</sup>  
~~70~~. The baseplate of claim <sup>30</sup>~~22~~ wherein the emitter tip comprises a material chosen from a group consisting of: SiC, Zr, La, Zn, TiN, LaB<sub>6</sub>, diamond and silicon oxycarbide.

<sup>43</sup>  
~~71~~. The display of claim <sup>46</sup>~~31~~ wherein:  
the emitter tips each comprise a material chosen from a group consisting of: SiC, Zr, La, Zn, TiN, LaB<sub>6</sub>, diamond and silicon oxycarbide; and  
the emitter bodies each comprise a cermet material. --